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BF256A/BF256B/BF256C

N-Channel RF Amplifiers

- This device is designed for VHF/UHF amplifiers.
- Sourced from process 50.



1 TO-92
1. Gate 2. Source 3. Drain

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	30	V
V_{GS}	Gate-Source Voltage	-30	V
I_{GF}	Forward Gate Current	10	mA
P_D	Total Device Dissipation @ $T_A=25^\circ\text{C}$ Derate above 25°C	350 2.8	mW mW/ $^\circ\text{C}$
T_{STG}	Operating and storage Temperature Range	- 55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$V_{DS} = 0, I_G = 1\mu\text{A}$	-30		V
V_{GS}	Gate-Source	$V_{DS} = 15\text{V}, I_D = 200\mu\text{A}$	-0.5	-7.5	V
$V_{GS(off)}$	Gate-Source Cutoff Voltage	$V_{DS} = 15\text{V}, I_D = 10\text{nA}$	-0.5	-8	V
I_{GSS}	Gate Reverse Current	$V_{GS} = -20\text{V}, V_{DS} = 0$		-5	nA
On Characteristics					
I_{DSS}	Zero-Gate Voltage Drain Current BF256A BF256B BF256C	$V_{GS} = 15\text{V}, V_{DS} = 0$	3 6 11	7 13 18	mA
Small Signal Characteristics					
gfs	Common Source Forward Transconductance	$V_{DS} = 15\text{V}, V_{GS} = 0, f = 1\text{KHz}$	4.5		mmhos

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